

P-Channel MOSFET

General Description

The WSK78P10 uses advanced SGT technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V.

This device is suitable for use as a Battery protection or in other Switching application.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Green Device Available

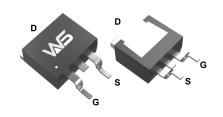
Product Summery

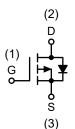
BV _{DSS}	R _{DS(ON)}	I _D
-100V	19mΩ	-78A

Applications

- Brushless motor
- Load switch.
- Uninterruptible power supply

TO-263-2L Pin Configuration





Absolute Maximum Ratings (T_C=25°C, Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-78	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ¹	-56	A
I _{DM}	Pulsed Drain Current ²	-300	
E _{AS}	Single Pulse Avalanche Energy ³	174	mJ
I _{AS}	Avalanche Current	-50	А
P _D @T _C =25°C	Total Power Dissipation ⁴	280	W
T _{STG}	Storage Temperature Range -55 to 150		°C
T _J	Operating Junction Temperature Range	-55 to 150	

Thermal Data

Symbol	Parameter	Rating	Units
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	°C/\\/
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹	0.65	°C/W



Electrical Characteristics (T_J=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250μA	-100			V	
D	Statia Prain Source On Resistance	V _{GS} =-10V , I _D =-20A		19	25	m0	
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-10A		25	30	mΩ	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250μA	-1.0	-1.6	-2.5	V	
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-100V , V _{GS} =0V			-1.0	μA	
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA	
Qg	Total Gate Charge			80			
Q_{gs}	Gate-Source Charge	V _{DS} =-50V , V _{GS} =-10V , I _D =-5A		15.6		nC	
Q_{gd}	Gate-Drain Charge			17.2			
$T_{d(on)}$	Turn-on Delay Time			26			
T _r	Rise Time	V _{DD} =-50V , V _{GS} =-10V ,		78		200	
T _{d(off)}	Turn-off Delay Time	$R_G=6\Omega$, $I_D=-5A$		210		ns	
T _f	Fall Time			200			
C _{iss}	Input Capacitance			4230			
C _{oss}	Output Capacitance	V_{DS} =-50V , V_{GS} =0V , f =1.0MHz		388		pF	
C _{rss}	Reverse Transfer Capacitance			26			

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
I _S	Continuous Source Current	V -V -OV Force Current			-80	_
I _{SM}	Pulsed Source Current	V _G =V _D =0V, Force Current			280	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =-30A			-1.2	V
t _{rr}	Reverse Recovery Time	L = EA di/dt=100A/us T =2E°C		208		ns
Q _{rr}	Reverse Recovery Charge	I _F =-5A , di/dt=100A/µs , T _J =25°C		560		nC

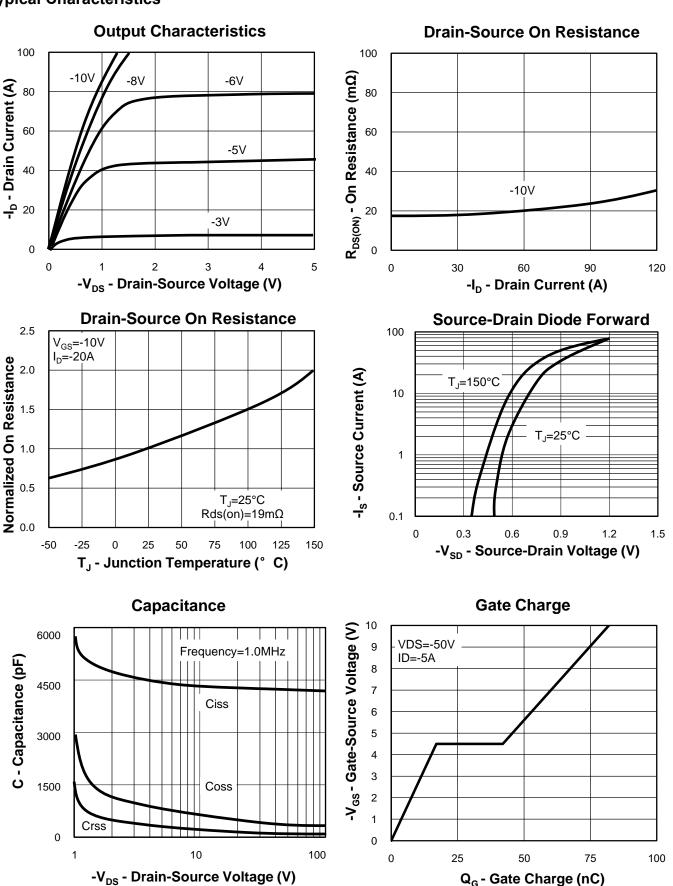
Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2. The data tested by pulsed, pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%.$
- 3. The E $_{\rm AS}$ data shows Max. rating. The test condition is $\rm\,V_{DD}$ =-72 $\rm\,V_{GS}$ =-10V, L=0.1mH, I $_{\rm AS}$ =-50A
- 4. The power dissipation is limited by 150°C junction temperature.
- 5. The data is theoretically the same as $\ I_D$ and $\ I_{DM}$, in real applications, should be limited by total power dissipation.



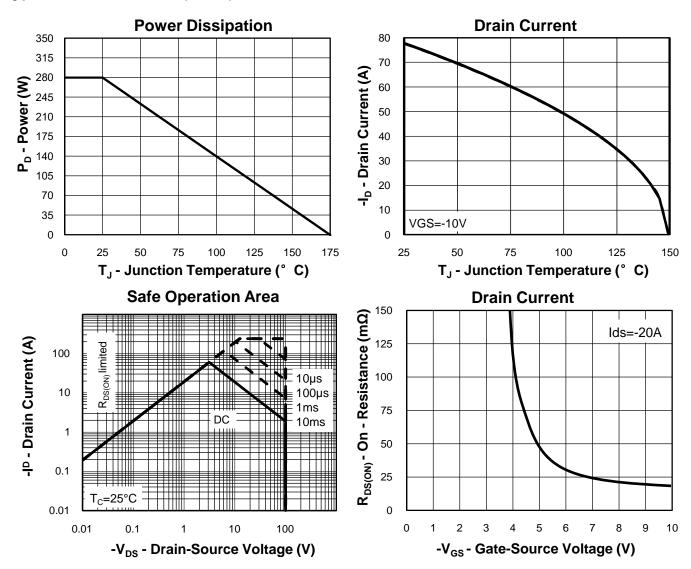


Typical Characteristics

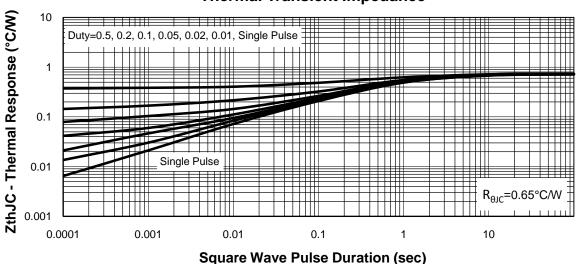




Typical Characteristics (Cont.)

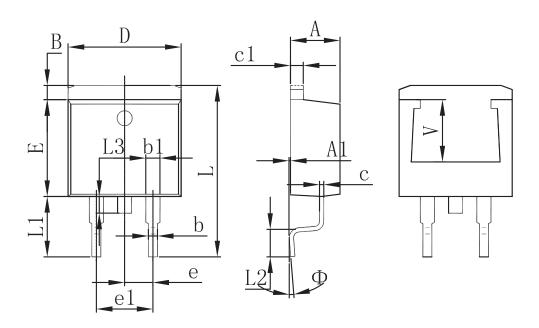


Thermal Transient Impedance





Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.120	1.420	0.044	0.056	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
L	14.940	15.500	0.588	0.610	
L1	4.950	5.450	0.195	0.215	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
Ф	0°	8°	0°	8°	
V	5.600 REF.		0.220	REF.	



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